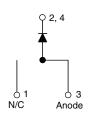


HEXFRED®, Ultrafast Soft Recovery Diode, 4 A





PRIMARY CHARACTERISTICS						
I _{F(AV)}	4 A					
V_{R}	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	17 ns					
T _J max.	150 °C					
Package	DPAK (TO-252AA)					
Circuit configuration	Single					

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Guaranteed avalanche
- · Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

Pb



ROHS

HALOGEN FREE

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _{RRM}		600	V		
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4			
Single pulse forward current	I _{FSM}		25	Α		
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16			
Maximum power dissipation	P _D	T _C = 100 °C	10	W		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage See fig. 1		I _F = 4 A	-	1.5	1.8	V	
	V_{F}	I _F = 8 A	-	1.8	2.2		
		I _F = 4 A, T _J = 125 °C	-	1.4	1.7		
Maximum reverse	,	$V_R = V_R$ rated	-	0.17	3.0		
leakage current	I _R	$T_J = 125 ^{\circ}\text{C}$, $V_R = 0.8 ^{\circ}\text{X}$ V_R rated	-	44	300	μΑ	
Junction capacitance	C _T	V _R = 200 V	-	4	8	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ	





DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		-	17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C	$I_F = 4 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	38	57		
Peak recovery current	I _{RRM}	T _J = 25 °C		=	2.9	5.2	А	
		T _J = 125 °C		-	3.7	6.7		
Povorce recovery charge	0	T _J = 25 °C		-	40	60	nC	
Reverse recovery charge	Q_{rr}	T _J = 125 °C		-	70	105	IIC	
Rate of fall of recovery current	dI _{(rec)M} /dt	T _J = 25 °C		=	280	-	Λ/μο	
		T _J = 125 °C		-	235	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- C/VV	
Majaht			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style DPAK (TO-252AA)		HFA04SD60S			

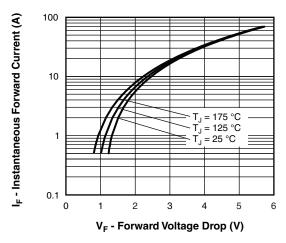


Fig. 1 - Typical Forward Voltage Drop Characteristics

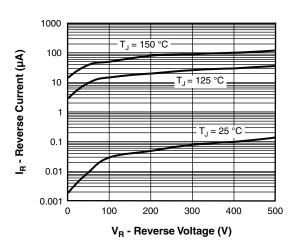


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

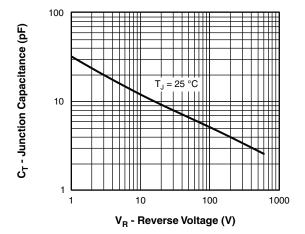


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

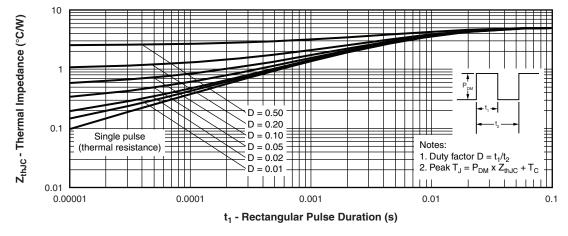


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



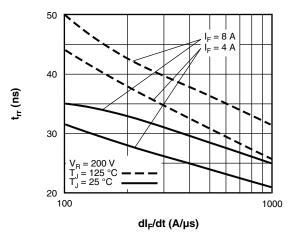


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

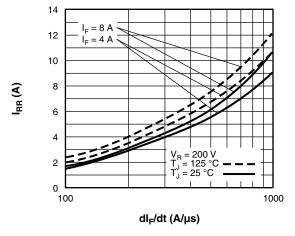


Fig. 6 - Typical Recovery Current vs. dl_F/dt

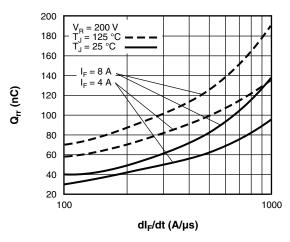


Fig. 7 - Typical Stored Charge vs. dl_E/dt

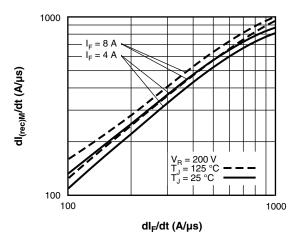


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

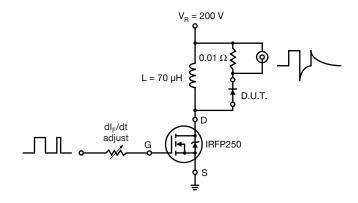
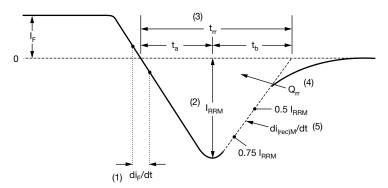


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{rr}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and $\mathbf{I}_{\mathrm{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

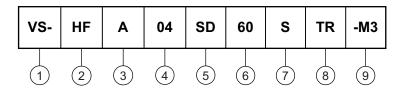
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

HEXFRED® family

3 - Electron irradiated

Current rating (04 = 4 A)

5 - D-PAK

6 - Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• R = tape and reel (right oriented)

• L = tape and reel (left oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

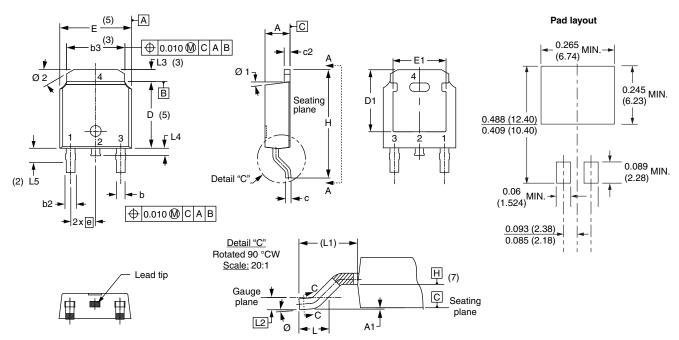
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA04SD60S-M3	75	3000	Antistatic plastic tube			
VS-HFA04SD60STR-M3	2000	2000	13" diameter reel			
VS-HFA04SD60SL-M3	3000	3000	13" diameter reel			
VS-HFA04SD60SR-M3	3000	3000	13" diameter reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95627				
Part marking information	www.vishay.com/doc?95176				
Packaging information	www.vishay.com/doc?95033				



D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



CVMPOL	SYMBOL MILLIMETERS INCHES		HES	NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	2.18	2.39	0.086	0.094		
A1	-	0.13	-	0.005		
b	0.64	0.89	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215	3	
С	0.46	0.61	0.018	0.024		
c2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245	5	
D1	5.21	-	0.205	-	3	
Е	6.35	6.73	0.250	0.265	5	
E1	4.32	-	0.170	-	3	

SYMBOL MILLIMETERS INCHE		HES	NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29 BSC		0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51 BSC		0.020 BSC		
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0° 10°		
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC® outline TO-252AA



Vishay

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